



# TECHNICAL DATA

## PNP POWER SILICON TRANSISTOR

Qualified per MIL-PRF-19500/514

### Devices

2N6274

2N6277

### Qualified Level

JAN  
JANTX  
JANTXV

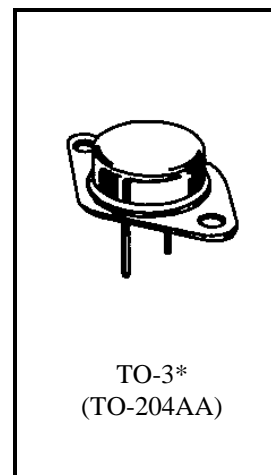
### MAXIMUM RATINGS

Ratings	Symbol	2N6274	2N6277	Unit
Collector-Emitter Voltage	$V_{CEO}$	100	150	Vdc
Collector-Base Voltage	$V_{CBO}$	120	180	Vdc
Emitter-Base Voltage	$V_{EBO}$	6.0		Vdc
Base Current	$I_B$	20		Adc
Collector Current	$I_C$	50		Adc
Total Power Dissipation	$P_T$	@ $T_C = +25^{\circ}C$ <sup>(1)</sup>	250	W
		@ $T_C = +100^{\circ}C$ <sup>(2)</sup>	143	W
Operating & Storage Junction Temperature Range	$T_j, T_{stg}$	-65 to +200		$^{\circ}C$

### THERMAL CHARACTERISTICS

Characteristics	Symbol	Max.	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.7	$^{\circ}C/W$

1) Derate linearly 1.43 W/ $^{\circ}C$  between  $T_C = +25^{\circ}C$  and  $T_C = +200^{\circ}C$



\*See appendix A for package outline

### ELECTRICAL CHARACTERISTICS ( $T_C = 25^{\circ}C$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
Collector-Emitter Breakdown Voltage $I_C = 50$ mAdc	2N6274	100	150	Vdc
	2N6277			
Collector-Emitter Cutoff Current $V_{CE} = 50$ Vdc	2N6274		50	$\mu$ Adc
	2N6277			
Collector-Emitter Cutoff Current $V_{CE} = 120$ Vdc, $V_{BE} = -1.5$ Vdc	2N6274		10	$\mu$ Adc
	2N6277			
Collector-Emitter Cutoff Current $V_{CE} = 180$ Vdc, $V_{BE} = -1.5$ Vdc	2N6274		10	$\mu$ Adc
	2N6277			
Emitter-Base Cutoff Current $V_{EB} = 6.0$ Vdc	$I_{EBO}$		100	$\mu$ Adc
Collector-Base Cutoff Current $V_{CB} = 120$ Vdc	2N6274		10	$\mu$ Adc
	2N6277			
Collector-Base Cutoff Current $V_{CB} = 180$ Vdc	2N6274		10	$\mu$ Adc
	2N6277			

**2N6274, 2N6277 JAN SERIES**
**ELECTRICAL CHARACTERISTICS (con't)**

Characteristics	Symbol	Min.	Max.	Unit
<b>ON CHARACTERISTICS <sup>(2)</sup></b>				
Forward-Current Transfer Ratio I <sub>C</sub> = 1.0 Adc, V <sub>CE</sub> = 4.0 Vdc I <sub>C</sub> = 20 Adc, V <sub>CE</sub> = 4.0 Vdc I <sub>C</sub> = 50 Adc, V <sub>CE</sub> = 4.0 Vdc	h <sub>FE</sub>	50 30 10	120	
Collector-Emitter Saturation Voltage I <sub>C</sub> = 20 Adc, I <sub>B</sub> = 2.0 Adc I <sub>C</sub> = 50 Adc, I <sub>B</sub> = 10 Adc	V <sub>CE(sat)</sub>		1.0 3.0	Vdc
Base-Emitter Saturation Voltage I <sub>C</sub> = 20 Adc, I <sub>B</sub> = 2.0 Adc	V <sub>BE(sat)</sub>		1.8	Vdc

**DYNAMIC CHARACTERISTICS**

Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio I <sub>C</sub> = 1.0 Adc, V <sub>CE</sub> = 10 Vdc, f = 10 MHz	h <sub>fe</sub>	3.0	12	
Output Capacitance V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz	C <sub>obo</sub>		600	pF

**SWITCHING CHARACTERISTICS**

Turn-On Time V <sub>CC</sub> = 80 Vdc; I <sub>C</sub> = 20 Adc; I <sub>B</sub> = 2.0 Adc	t <sub>on</sub>		0.5	μs
Turn-Off Time V <sub>CC</sub> = 80 Vdc; I <sub>C</sub> = 20 Adc; I <sub>B1</sub> = -I <sub>B2</sub> = 2.0 Adc	t <sub>off</sub>		1.05	μs

**SAFE OPERATING AREA**

<b>DC Tests</b> T <sub>C</sub> = +25 <sup>0</sup> C, 1 Cycle, t = 1.0 s		
<b>Test 1</b> V <sub>CE</sub> = 5.0 Vdc, I <sub>C</sub> = 50 Adc	All Types	
<b>Test 2</b> V <sub>CE</sub> = 8.6 Vdc, I <sub>C</sub> = 165 mAdc	All Types	
<b>Test 3</b> V <sub>CE</sub> = 80 Vdc, I <sub>C</sub> = 29 mAdc	2N6274	
	<b>Test 4</b>	
V <sub>CE</sub> = 120 Vdc, I <sub>C</sub> = 110 mAdc	2N6277	

(2) Pulse Test: Pulse Width = 300μs, Duty Cycle ≤ 2.0%.

